**TOSHIBA** 

TOSHIBA Photocoupler GaAłAs IRed & Photo IC

# **TLP558**

Isolated Bus Driver High Speed Line Receiver Microprocessor System Interfaces MOS FET Gate Driver Transistor Inverter

The TOSHIBA TLP558 consists of a GaAlAs light emitting diode and integrated high gain, high speed photodetector.

This unit is 8-lead DIP package.

The detector has a three state output stage that provides source drive and sink drive, and built-in schmitt trigger. The detector IC has an internal shield that provides a guaranteed common mode transient immunity of  $1000V/\mu s$ . TLP558 is inverter logic type. For buffer logic type, TLP555 is in line-up,

- Input current: IF=1.6 mA (max)
- Power supply voltage: VCC=4.5 to 20 V
- Switching speed: tpHL, tpLH=400ns (max)
- Common mode transient immunity: ±1000V/µs (min)/
- Guaranteed performance over temperature: -25 to 85°C
- Isolation voltage: 2500Vrms (min)

**Truth Table** 

Input

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8 and 5.

• UL recognized: UL1577, file No. E67349

Enable

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 c-UL approved : CSA Component Acceptance Service No. 5A, File No.E67349

Output

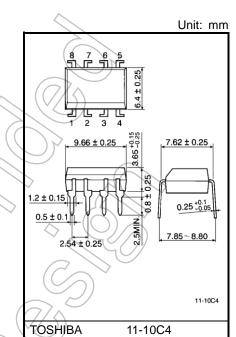
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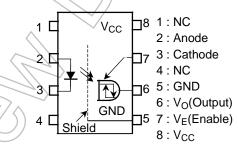
Ζ

A 0.1µF bypass capacitor must be connected between pins

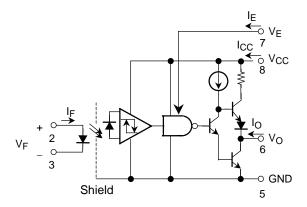


Weight: 0.54 g (typ.)

# Pin Configuration (top view)



#### Schematic



Start of commercial production 1987-05

# 2017-05-18

### **Absolute Maximum Ratings**

	Charactersitic	Symbol	Rating	Unit		
	Forward current		١F	10	mA	
ED	Peak transient forward current	(Note 1)	IFPT	IFPT 1		
Щ	Reverse voltage		VR	<u>√</u> 5	V	
	Diode power dissipation		PD	45	mW	
	Output current		lo	40/-25	mA	
	Peak output current	(Note 2)	IOP	80/-50	mA	
	Output voltage		Vo	-0.5 to 20	V	
ъ	upply voltage		Vcc	-0.5 to 20	V	
Detector	Three state enabel voltage		VE	-0.5 to 20	V	
ă	Output power dissipation		Po	100	mW	
	Output power dissipation derating (Ta > 70 °C)		ΔΡΟ/ΔΤα	-1.8	mW/ºC	
	Total package power dissipation		PT	200	mW	
	Total package power dissipation derating (Ta > 70 °C)	$(\bigcirc$	ΔΡΤ/ΔΤα	-3.6	mW/°C	
Ope	arating temperature range		Topr	-40 to 85	°C	
Stor	age temperature range	T <sub>stg</sub>	-55 to 125	C		
Lea	d solder temperature(10s)	T <sub>sol</sub>	260	°C		
Isol	ation voltage (AC, 60 s, R.H. ≤ 60%, Ta=25°C)	BVs	2500	Vrms		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Pulse width  $\leq$  1µs, 300pps.
- Note 2: Pulse width  $\leq$  5µs, duty ratio  $\leq$  0.025.
- Note 3: 1.6mm below seating plane.
- Note 4: Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min	Тур.	Max	Unit
Input current, on	IF(ON)	2 (Note 1)	_	5	mA
Input voltage, off	VF(OFF)	0	—	0.8	V
Supply voltage	Vcc	4.5	—	20	V
Enable voltage high	VEH	2.0	—	20	V
Enable voltage low	VEL	0	—	0.8	V
Fan out(TTL load)	N	_	—	4	—
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 1: 2mA condition permits at least 20% CTR degradation guardband. Initial switching threshold is 1.6mA or less.

#### Electrical Characteristics (unless otherwise specified, Ta = -25 to 85°C, Vcc = 4.5 to 20V)

							1
Characteristic	Symbol	Test Con	Min	Тур.	Max	Unit	
Input forward voltage	VF	IF=5mA, Ta=25°C		_	1.55	1.7	V
Temperature coefficient of forward voltage	ΔV <sub>F</sub> / ΔTa	IF=5mA		$\overline{\langle}$	-2.0	_	mV / °C
Input reverse current	I <sub>R</sub>	V <sub>R</sub> =5V, Ta=25°C		->		10	μA
Input capacitance	CT	V <sub>F</sub> =0V, f=1MHz, Ta	a=25°C		45	—	pF
Output leakage current	Юнн	vF-0v,	/o=VE=5.5V		$\sum_{i=1}^{n}$	100	μA
(Vo > Vcc)		VCC=4.5V V	/o=VE=20V	(4)	0.01	500	μ. ι
Logic low output voltage	Vol	I <sub>OL</sub> =6.4mA, I <sub>F</sub> =1.6r V <sub>E</sub> =2V	mA		0.4	0.5	V
Logic high output voltage	Vон	I <sub>OH</sub> =-2.6mA, V <sub>F</sub> =0. V <sub>E</sub> =2V	8V	2.4	3.3	_	V
Logic low enable current	I <sub>EL</sub>	V <sub>E</sub> =0.4V		—	-0.13	-0.32	mA
		VE=2.7V		—		20	
Logic high enable current	IEH	V <sub>E</sub> =5.5V	( )	$\langle \nabla \rangle$	$\mathcal{A}$	100	μA
		V <sub>E</sub> =20V		_	0.01	250	
Logic low enable voltage	VEL		$\checkmark$	R	) }	0.8	V
Logic high enable voltage	VEH	$\langle \langle \rangle \rangle$	$\geq$	2.0	- V	_	V
Logia low gupply gurrant	ICCL	V <sub>CC</sub> =V <sub>E</sub> =5.5V		77*	4.0	6.0	- mA
Logic low supply current		IF=5mA V	/cc=VE=20V	9	4.6	7.5	IIIA
Logic high supply current	Іссн	VF=QV	CC=VE=5.5V	_	4.2	6.0	mA
		VF=0V	/CC=VE=20V	—	4.7	7.5	
	lozi	VF=0V VE=0.8V	V <sub>O</sub> =0.4V	_	_	-20	
High impedance state output current	$(\bigcirc)$		V <sub>O</sub> =2.4V	_	—	20	μA
	Іодн	IF=5mA VE=0.8V	V <sub>O</sub> =5.5V	_	_	100	
	$\langle \bigcirc \rangle$		V <sub>O</sub> =20V		1	500	
Logic low short circuit	losL		V <sub>O</sub> =V <sub>CC</sub> =5.5V 25		55	_	mA
output current (Note 1)	- IUSL	VE=2V V	/o=V <sub>CC</sub> =20V	40	80	_	IIIA
Logic high short circuit		VF=0V, VO=GND	V <sub>CC</sub> =5.5V	-10	-25	_	mA
output current (Note 1)	Іозн	V <sub>E</sub> =2V	V <sub>CC</sub> =20V	-25	-60	_	
Input current logic low output	IFL	V <sub>E</sub> =2V, I <sub>O</sub> =6.4mA V <sub>O</sub> < 0.4V		_	0.4	1.6	mA
Input voltage logic high output	VFH	V <sub>E</sub> =2V, I <sub>O</sub> =-2.6mA V <sub>O</sub> > 2.4V		0.8	—	_	V
Input current hysteresis	( IHYS	V <sub>CC</sub> =V <sub>E</sub> =5V		_	0.05	_	mA
Resistance (input-output)	Rs	Vs=500V, R.H. ≤60 Ta=25°C	)% (Note 2)	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Capacitance(input-output)	Capacitance(input-output) Cs Vs=0V, f=1MHz, Ta=25°C (Note 2			_	1.0	_	pF

Note: All typical values are at Ta=25°C, VCC=5V, IF(ON)=3mA unless otherwise specified.

Note 1: Duration of output short circuit time should not exceed 10ms.

Note 2: Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

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#### Switching Characteristics (unless otherwise specified, Vcc = 4.5 to 20V, Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time to logic high output	(Note 1)	tpLH		IF=3→ 0mA	_	250	400	ns
Propagation delay time to logic low output	(Note 1)	tpHL	1	IF=0→ 3mA		270	400	ns
Output rise time (10-90%)		tr		IF=3→ 0mA, V <sub>CC</sub> =5V	-(-	35	75	ns
Output fall time (90-10%)		tf		IF=0→ 3mA, V <sub>CC</sub> =5V		20	75	ns
Common mode transient immunity at logic high output	(Note 2)	Смн	2	IF=0mA, V <sub>CM</sub> =50V V <sub>O (Min)</sub> =2V	1000	_	_	V / µs
Common mode transient immunity at logic low output	(Note 2)	C <sub>ML</sub>	3	IF=1.6mA, V <sub>CM</sub> =50V V <sub>O (Max)</sub> =0.8V	-1000	_ ((	-	V / µs

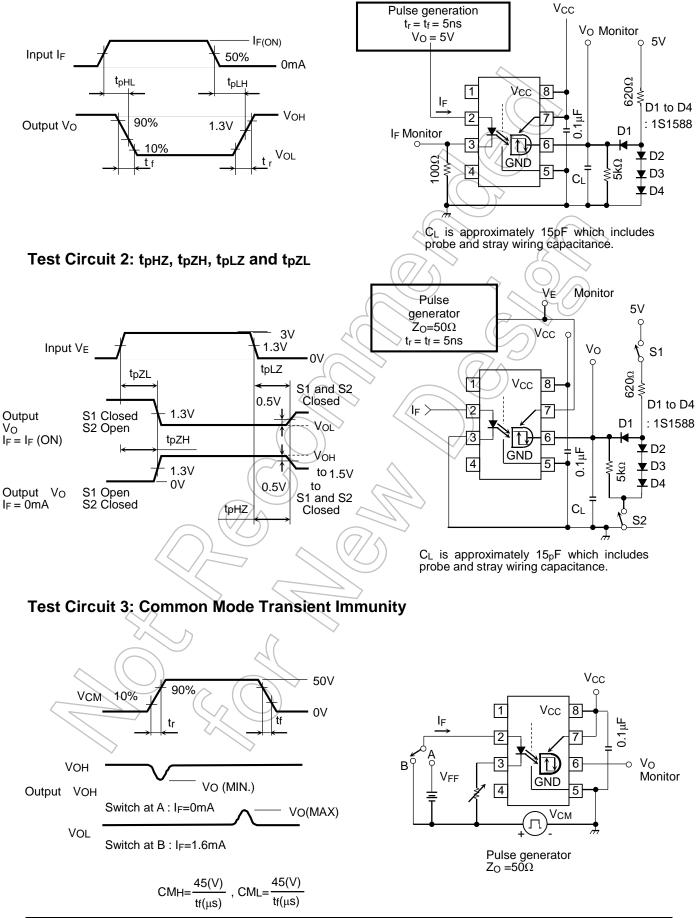
Note: All typical values are at Ta=25°C, Vcc=5V

- Note: A ceramic capacitor (0.1µF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.
- Note 1: The t<sub>pLH</sub> propagation delay is measured from the 50% point on the trailing edge of the input pulse to the 1.3V point on the leading edge of the output pulse. The t<sub>pHL</sub> propagation delay is measured from the 50% point on the leading edge of the input pulse to the 1.3V point on the trailing edge of the output pulse.
- Note 2: C<sub>ML</sub> is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state (V<sub>O</sub> < 0.8V).

 $C_{MH}$  is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic state (V<sub>O</sub> > 2.0V).

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# Test Circuit 1: tpLH, tpHL, tr and tf



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